Single, Dual, Quad Low Voltage, Rail-to-Rail Operational Amplifiers

The LMV821, LMV822, and LMV824 are operational amplifiers with low input voltage offset and drift vs. temperature. In spite of low quiescent current requirements these devices have 5 MHz bandwidth and 1.4 V/µs slew rate. In addition they provide rail–to–rail output swing into 600 Ω loads. The input common–mode voltage range includes ground, and the maximum input offset voltage is only 3.5 mV. Substantially large capacitive loads can be driven by simply adding a pullup resistor or isolation resistor.

The LMV821 (single) is available in a space–saving SC70–5 while the dual and quad also come in ultra small SOIC and TSSOP packages.

Features

Low Offset Voltage: 3.5 mV
Very low Offset Drift: 1.0 μV/°C

• High Bandwidth: 5 MHz

 $\bullet\;$ Rail–to–Rail Output Swing into a 600 Ω load

• Capable of driving highly capacitive loads

• These Devices are Pb-Free and are RoHS Compliant

Typical Applications

• Notebook Computers

• PDAs

• Modem Transmitter/ Receivers

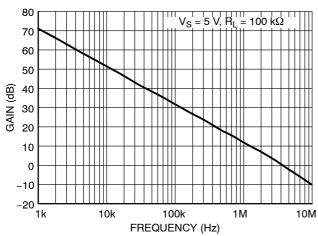


Figure 1. Gain vs. Frequency



ON Semiconductor®

http://onsemi.com



SC-70 CASE 419A



Micro8[™] CASE 846A



SOIC-8 CASE 751



SOIC-14 CASE 751A



TSSOP-14 CASE 948G

ORDERING AND MARKING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

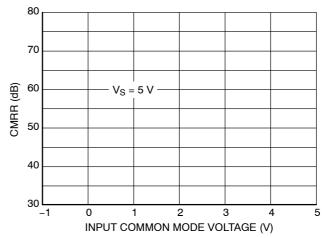
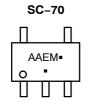


Figure 2. CMRR vs. Input Common Mode Voltage

MARKING DIAGRAMS



AAE = Specific Device Code

M = Date Code ■ Pb-Free Package

(Note: Microdot may be in either location)

8 H H V822 AYW-

V822 = Specific Device Code

A = Assembly Location Y = Year

W = Work Week ■ Pb-Free Package

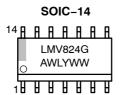
(Note: Microdot may be in either location)

V822 = Specific Device Code A = Assembly Location

L = Wafer Lot
Y = Year
W = Work Week

W = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

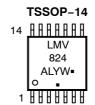


LMV824 = Specific Device Code

A = Assembly Location

WL = Wafer Lot Y = Year

WW = Work Week
G = Pb-Free Package



LMV824 = Specific Device Code

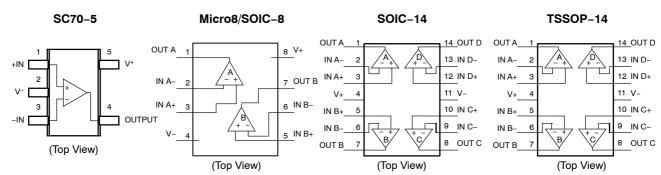
A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

■ = Pb-Free Package (Note: Microdot may be in either location)

PIN CONNECTIONS



MAXIMUM RATINGS

Symbol	Rating	Value	Unit
Vs	Supply Voltage (Operating Range V _S = 2.7 V to 5.5 V)	5.5	V
V_{IDR}	Input Differential Voltage	± Supply Voltage	V
V _{ICR}	Input Common Mode Voltage Range	-0.5 to (V+) +0.5	V
	Maximum Input Current	10	mA
t _{SO}	Output Short Circuit (Note 1)	Continuous	
TJ	Maximum Junction Temperature (Operating Range -40°C to 85°C)	150	°C
θ_{JA}	Thermal Resistance		°C/W
	SC-70	280	1
	Micro8	238	1
	SOIC-8	212	1
	SOIC-14	156	1
	TSSOP-14	190	1
T _{STG}	Storage Temperature	-65 to 150	°C
	Mounting Temperature (Infrared or Convection – 20 sec)	235	°C
V _{ESD}	ESD Tolerance Machine Model Human Body Model	200 2000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Continuous short–circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Shorting output to either V+ or V- will adversely affect reliability.

2.7V DC ELECTRICAL CHARACTERISTICS Unless otherwise noted, all min/max limits are guaranteed for T_A = 25°C, V+ = 2.7 V, V- = 0 V, V_{CM} = V+/2, V_{O} = V+/2 and R_{L} > 1 M Ω . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}			1	3.5	mV
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			4	
Input Offset Voltage Average Drift	TCV _{OS}			1		μV/°C
Input Bias Current	I _B			105	210	nA
	[$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			315	
Input Offset Current	I _{IO}			0.5	30	nA
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			50	
Common-Mode Rejection	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 1.7 \text{ V}$	70	85		dB
Ratio		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	68			
Power Supply Rejection Ratio	PSRR	$1.5 \text{ V} \le \text{V+} \le 4 \text{ V}, \text{V} - = -1 \text{ V}, \text{V}_{\text{O}} = 0 \text{ V}, \\ \text{V}_{\text{CM}} = 0.0 \text{ V}$	75	85		dB
	[$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	70			
Input Common-Mode Voltage Range	V _{CM}	For CMRR ≥ 53 dB and T _A = -40° C to $+85^{\circ}$ C	-0.2	-0.3 to 2.0	1.9	V
Large Signal Voltage Gain	AV	R_L = 600 Ω , V_O = 0.5 V to 2.5 V	80	95		dB
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	70			
		R_L = 2 k Ω , V_O = 0.5 V to 2.5 V	83	89		
	[$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
Output Swing	V _{OH}	R_L = 600 Ω to 1.35 V	2.5	2.58		V
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	2.4			
	V _{OL}	R_L = 600 Ω to 1.35 V		0.13	0.21	
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			0.3	
	V _{OH}	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$	2.6	2.66		
		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	2.5			
	V _{OL}	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$		0.08	0.12	
	[$T_A = -40^{\circ}C$ to $+85^{\circ}C$			0.2	
Output Current	I _O	Sourcing, V _O = 0 V	12			mA
		Sinking, V _O = 2.7 V	12	26		
Supply Current	I _{CC}	LMV821 (Single)		0.242	0.3	mA
		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			0.5	
		LMV822 (Both Applications)		0.5	0.7	
		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			0.9	
		LMV824 (All Four Applications)		1	1.3	
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			1.5	

 $\textbf{2.5V DC ELECTRICAL CHARACTERISTICS} \ \ \textbf{Unless otherwise noted, all min/max limits are guaranteed for } T_A = 25 ^{\circ}C, \ V+ = 2.5 \ V,$ $V_- = 0 \text{ V, V}_{CM} = V_+/2, V_O = V_+/2 \text{ and R}_L > 1 \text{ M}\Omega. \text{ Typical specifications represent the most likely parametric norm. Min/Max}$ specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		1	3.5	mV
					4	
Output Swing	V _{OH}	R_L = 600 Ω to 1.25 V	2.3	2.37		V
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	2.2			1
	V _{OL}	R_L = 600 Ω to 1.25 V		0.13	0.20	1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.3	1
	V _{OH}	R_L = 2 k Ω to 1.25 V	2.4	2.46		1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	2.3			1
	V _{OL}	R_L = 2 k Ω to 1.25 V		0.08	0.12	
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			0.20	1

 $\textbf{2.7V AC ELECTRICAL CHARACTERISTICS} \ \ \textbf{Unless otherwise specified, all limits are guaranteed for } \ T_A = 25^{\circ}C, \ V_{+} = 2.7 \ V, \ V_{-} = 2.7 \ V, \ V_$ 0 V, V_{CM} = 1.0 V, V_{O} = V+/2 and RL > 1 M Ω . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Slew Rate	SR	(Note 2)		1.5		V/uS
Gain Bandwidth Product	GBWP			5		MHz
Phase Margin	θ_{m}			55		0
Gain Margin	G _m			12.9		dB
Input-Referred Voltage Noise	e _n	f = 1 kHz, V _{CM} = 1 V		12		nV/√ Hz
Input-Referred Current Noise	i _n	f = 1kHz		0.2		pA/√ Hz
Total Harmonic Distortion	THD	f = 1 kHz, AV = -2, R_L = 10 k Ω , V_O = 1.8 V_{PP}		0.023		%
Amplifier-to-Amplifier Isolation		(Note 3)		135		dB

^{2.} Connected as voltage follower with input step from 0.5 V to 1.5 V. Number specified is the average of the positive and negative slew rates.

3. Input referred, $R_L = 100 \text{ k}\Omega$ connected to V+/2. Each amp excited in turn with 1kHz to produce $V_O = 3 \text{ V}_{PP}$. For Supply Voltages < 3 V, $V_0 = V+$.

5V DC ELECTRICAL CHARACTERISTICS Unless otherwise noted, all min/max limits are guaranteed for $T_A = 25^{\circ}C$, $V_+ = 5$ V, $V_- = 0$ V, VCM = V+/2, $V_O = V_- = 0$ V, VCM = V+/2 and $R_L > 1$ M Ω . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}			1	3.5	mV
		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			4	
Input Offset Voltage Average Drift	TCV _{OS}			1		μV/°C
Input Bias Current	Ι _Β			119	245	nA
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			380	
Input Offset Current	I _{IO}			0.5	30	nA
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			50	
Common-Mode Rejection	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 4.0 \text{ V}$	72	90		dB
Ratio		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	70			
Power Supply Rejection Ratio	PSRR	$1.7 \text{ V} \leq \text{V+} \leq 4 \text{ V}, \text{V} -= 1 \text{ V}, \text{V}_{O} = 0 \text{ V}, \\ \text{V}_{CM} = 0.0 \text{ V}$	75	85		dB
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	70			
Input Common–Mode Voltage Range	V _{CM}	For CMRR \geq 58 dB and T _A = -40° C to $+85^{\circ}$ C	-0.2	-0.2 to 4.3	4.2	V
Large Signal Voltage Gain	A_{V}	R_L = 600 Ω , V_O = 1.0 V to 4.0 V	87	100		dB
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	73			
		R_L = 2 k Ω , V_O = 1.0 V to 4.0 V	84	99		
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	82			
Output Swing	V _{OH}	R_L = 600 Ω to 2.5 V	4.75	4.84		٧
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	4.7			
	V _{OL}	R_L = 600 Ω to 2.5 V		0.17	0.33	
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.4	
	V _{OH}	RL = 2 k Ω to 2.5 V	4.85	4.9		
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	4.8			
	V _{OL}	$R_L = 2 \text{ k}\Omega \text{ to } 2.5 \text{ V}$		0.1	0.15	
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.2	
Output Current	I _O	Sourcing, Vo = 0 V	20	45		mA
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	10			-
		Sinking, Vo = 5 V	20	40		-
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	15			-
Supply Current	Icc			0.3	0.4	mA
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.6	
		LMV822 (Both Applications)		0.5	0.7	1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.9	1
		LMV824 (All Four Applications)		1	1.3	1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			1.5	1

5V AC ELECTRICAL CHARACTERISTICS Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V_+ = 5$ V, $V_- = 0$ V, $V_{CM} = 2.0$ V, $V_O = V_+/2$ and $R_L > 1$ M Ω . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Slew Rate	SR	(Note 4)		2		V/μS
Gain Bandwidth Product	GBWP			5.6		MHz
Phase Margin	θ_{m}			63		0
Gain Margin	G _m			11.7		dB
Input-Referred Voltage Noise	e _n	f = 1 kHz, V _{CM} = 1 V		11		nV/√ Hz
Input-Referred Current Noise	i _n	f = 1 kHz		0.21		pA/√ Hz
Total Harmonic Distortion	THD	f = 1 kHz, A_V = -2, R_L = 10 k Ω , V_O = 4.11 VPP		0.012		%
Amplifier-to-Amplifier Isolation		(Note 5)		135		dB

^{4.} Connected as voltage follower with input step from 0.5 V to 3.5 V. Number specified is the average of the positive and negative slew rates.

^{5.} Input referred, $R_L = 100 \text{ k}\Omega$ connected to V+/2. Each amp excited in turn with 1 kHz to produce $V_O = 3 \text{ V}_{PP}$. (For Supply Voltages < 3 V, $V_O = V_{PP}$).

TYPICAL PERFORMANCE CHARACTERISTICS

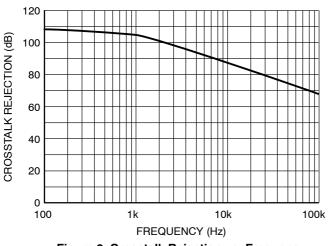


Figure 3. Crosstalk Rejection vs. Frequency

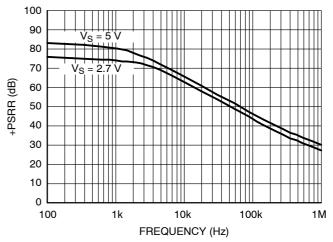


Figure 4. +PSRR vs. Frequency

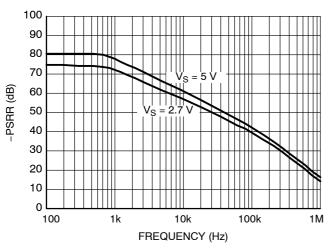


Figure 5. -PSRR vs. Frequency

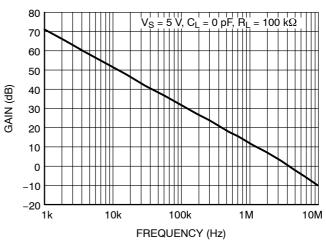


Figure 6. Gain vs. Frequency

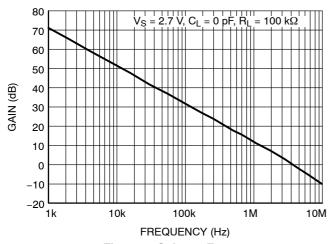


Figure 7. Gain vs. Frequency

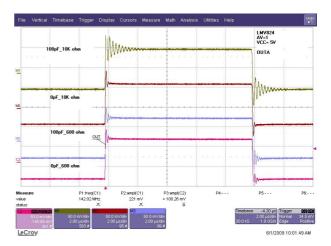


Figure 8. Non-Inverting Stability vs.
Capacitive Load

TYPICAL PERFORMANCE CHARACTERISTICS

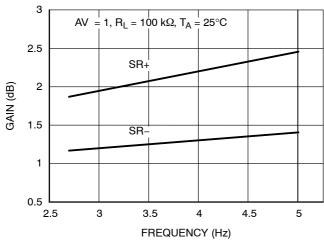


Figure 9. Gain vs. Frequency



Figure 10. Non-Inverting Large Signal Step Response



Figure 11. Non-Inverting Small Signal Step Response



Figure 12. Inverting Large Signal Step Response

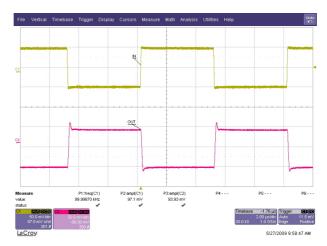


Figure 13. Inverting Small Signal Step Response

APPLICATIONS INFORMATION

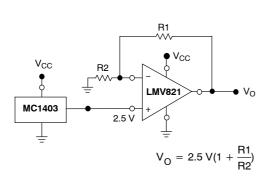


Figure 14. Voltage Reference

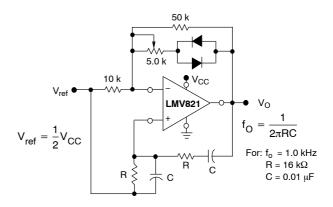


Figure 15. Wien Bridge Oscillator

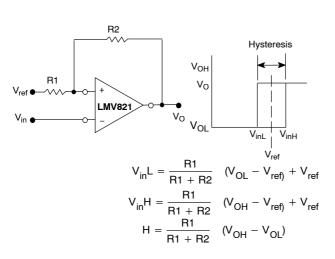
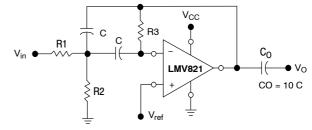


Figure 16. Comparator with Hysteresis



Given: f_0 = center frequency $A(f_0)$ = gain at center frequency

Choose value
$$f_o$$
, C
Then: $R3 = \frac{Q}{\pi f_O C}$

$$R1 = \frac{R3}{2 \, A(f_O)}$$

$$R2 = \frac{R1 \, R3}{4 \, Q^2 \, R1 \, - \, R3}$$

For less than 10% error from operational amplifier, (($Q_O f_O$)/BW) < 0.1 where f_o and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 17. Multiple Feedback Bandpass Filter

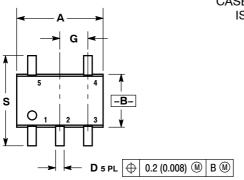
ORDERING INFORMATION

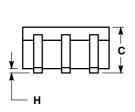
Order Number	Number of Channels	Specific Device Marking	Package Type	Shipping [†]
Order Number	Citatilleis	Specific Device Marking	Раскаде туре	Silippilig
LMV821SQ3T2G*	Single	AAE	SC-70 (Pb-Free)	3000 / Tape & Reel
LMV822DMR2G*	Dual	V822	Micro8 (Pb-Free)	4000 / Tape & Reel
LMV822DR2G*	Dual	V822	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LMV824DR2G	Quad	LMV824	SOIC-14 (Pb-Free)	2500 / Tape & Reel
LMV824DTBR2G	Quad	LMV 824	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

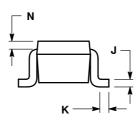
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*Contact factory.

PACKAGE DIMENSIONS

SC-88A, SOT-353, SC-70 CASE 419A-02 **ISSUE J**





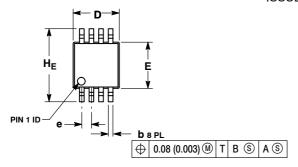


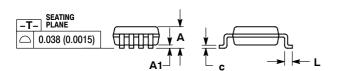
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

		INC	HES	MILLIN	IETERS
	DIM	MIN	MAX	MIN	MAX
	Α	0.071	0.087	1.80	2.20
	В	0.045	0.053	1.15	1.35
	С	0.031	0.043	0.80	1.10
Г	D	0.004	0.012	0.10	0.30
	G	0.026	BSC	0.65	BSC
	Н		0.004		0.10
	J	0.004	0.010	0.10	0.25
	K	0.004	0.012	0.10	0.30
	N	0.008	REF	0.20 REF	
Г	S	0.079	0.087	2.00	2.20

PACKAGE DIMENSIONS

Micro8TM CASE 846A-02 **ISSUE H**

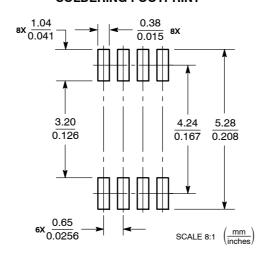




- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 846A-01 OBSOLETE, NEW STANDARD 846A-02.

	М	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX	
Α			1.10			0.043	
A1	0.05	0.08	0.15	0.002	0.003	0.006	
b	0.25	0.33	0.40	0.010	0.013	0.016	
C	0.13	0.18	0.23	0.005	0.007	0.009	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	2.90	3.00	3.10	0.114	0.118	0.122	
е		0.65 BSC		0.026 BSC			
L	0.40	0.55	0.70	0.016	0.021	0.028	
HE	4.75	4.90	5.05	0.187	0.193	0.199	

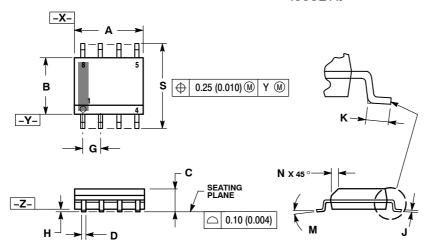
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

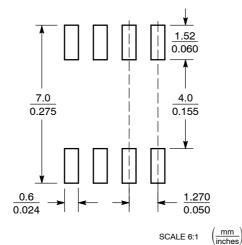
PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 **ISSUE AJ**



⊕ 0.25 (0.010) M Z YS XS

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

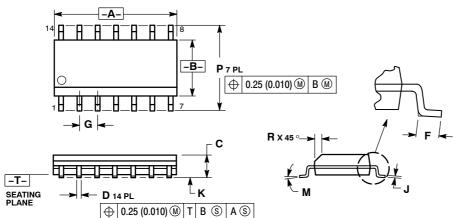
SCALE 6:1

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 751-01 THRU 751-06 ARE OBSOLETE. NEW
 STANDARD IS 751-07.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

PACKAGE DIMENSIONS

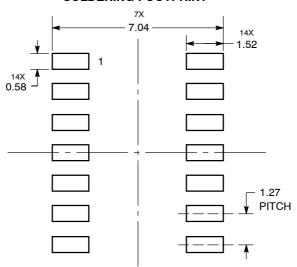
SOIC-14 CASE 751A-03 **ISSUE J**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAXIMUM MOLD PHOTHUSION 0.13 (0.00 PER SIDE.)
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION: ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

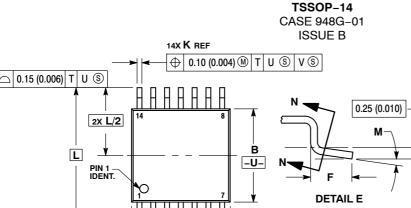
SOLDERING FOOTPRINT*



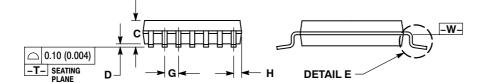
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



○ 0.15 (0.006) T △ 0.15 (0.006) T U S Α -V-



NOTES

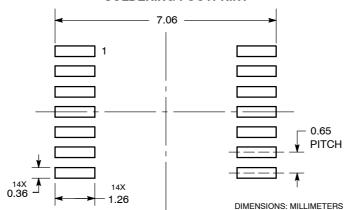
- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT

SECTION N-N

J J1



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